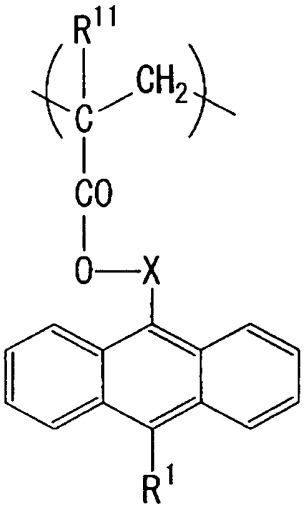
What is claimed is:

1. A base material for lithography comprising a component (a), a component (b), and a component (c) described below:

(a) a cross linking agent;

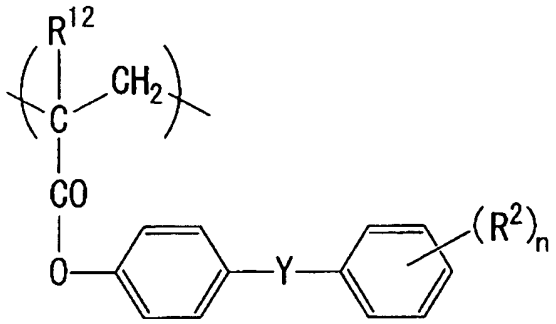
(b) a copolymer comprising a (meth)acrylate ester unit represented by a general formula (1) shown below,



• • • (1)

wherein, R^1 represents a hydrogen atom, a halogen atom, a hydroxyl group, a carboxyl group, or a hydrocarbon group of 1 to 5 carbon atoms that is substituted with at least one of a halogen atom, a hydroxyl group and a carboxyl group; X represents an alkyl chain of 1 to 4 carbon atoms; and R^{11} represents a hydrogen atom or a methyl group,

and a (meth)acrylate ester unit represented by a general formula (2) shown below,

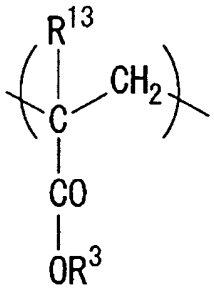


• • • (2)

wherein, R^2 represents a hydroxyl group, a carboxyl group, or a hydrocarbon group of 1 to 5 carbon atoms that is substituted with at least one of a hydroxyl group and a carboxyl group; Y represents $-SO_2-$, -CO- or -SO-; n represents a number from 1 to 4; and R^{12} represents a hydrogen atom or a methyl group; and

(c) an organic solvent.

2. A base material for lithography according to claim 1, wherein said component (b) is a copolymer that also comprises a (meth)acrylate ester unit represented by a general formula (3) shown below:



• • • (3)

wherein, R^3 represents a hydrocarbon group of 1 to 5 carbon atoms; and R^{13} represents a hydrogen atom or a methyl group.

3. A base material for lithography according to claim 1, wherein said component (a) is a nitrogen containing compound with an amino group and/or an imino group, and within all said amino groups and/or imino groups of said nitrogen containing compound, at least 2 hydrogen atoms are substituted with hydroxyalkyl groups and/or alkoxyalkyl groups.

4. A base material for lithography according to claim 3, wherein said component (a) is a condensation reaction product of said hydroxyalkyl group and/or alkoxyalkyl group with a monohydroxymonocarboxylic acid.

5. A base material for lithography according to claim 4, wherein in said monohydroxymonocarboxylic acid, a hydroxyl group and a carboxyl group are either bonded to an identical carbon atom, or bonded to two adjacent carbon atoms.

6. A base material for lithography according to claim 5, wherein said monohydroxymonocarboxylic acid is at least one compound selected from a group consisting of mandelic acid, lactic acid, and salicylic acid.

7. A base material for lithography according to claim 1, further comprising a light absorbing component (d).

8. A base material for lithography according to claim 7, wherein said component (d) is at least one compound selected from a group consisting of anthracene based compounds, sulfone based compounds, sulfoxide based compounds and benzophenone based

compounds containing at least 1 substituent group selected from a group consisting of hydroxyl group, hydroxyalkyl groups, alkoxyalkyl groups, and carboxyl groups.

9. A method of producing a resist pattern comprising the steps of: providing a lithography base material layer on top of a substrate by applying a base material for lithography according to any one of claim 1 through claim 8, and conducting heating to effect a cross linking reaction; providing a photoresist layer on top of said lithography base material layer; conducting light exposure; and developing said photoresist layer to form a resist pattern.